

LM3046 Transistor Array

General Description

The LM3046 consists of five general purpose silicon NPN transistors on a common monolithic substrate. Two of the transistors are internally connected to form a differentially-connected pair. The transistors are well suited to a wide variety of applications in low power system in the DC through VHF range. They may be used as discrete transistors in conventional circuits however, in addition, they provide the very significant inherent integrated circuit advantages of close electrical and thermal matching. The LM3046 is supplied in a 14-lead molded small outline package.

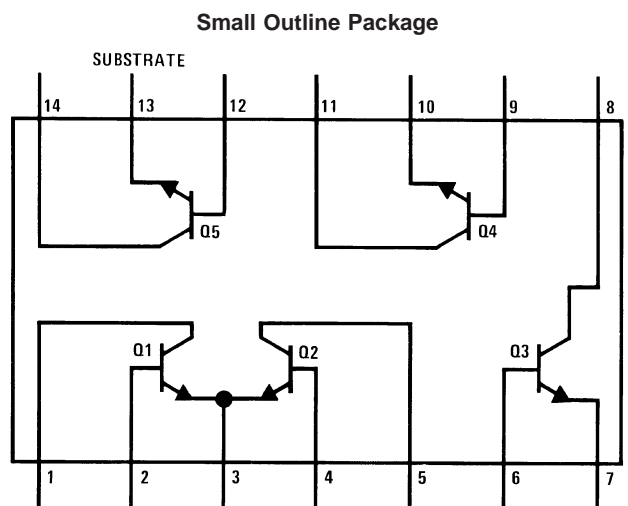
Features

- Two matched pairs of transistors
 V_{BE} matched ± 5 mV
 Input offset current $2 \mu\text{A}$ max at $I_C = 1 \text{ mA}$
- Five general purpose monolithic transistors
- Operation from DC to 120 MHz
- Wide operating current range
- Low noise figure: 3.2 dB typ at 1 kHz

Applications

- General use in all types of signal processing systems operating anywhere in the frequency range from DC to VHF
- Custom designed differential amplifiers
- Temperature compensated amplifiers

Schematic and Connection Diagram



DS007950-1

Top View
Order Number LM3046M
See NS Package Number M14A

Absolute Maximum Ratings (Note 1)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/Distributors for availability and specifications. ($T_A = 25^\circ\text{C}$)

	LM3046		Units
	Each Transistor	Total Package	
Power Dissipation:			
$T_A = 25^\circ\text{C}$	300	750	mW
$T_A = 25^\circ\text{C}$ to 55°C	300	750	mW
$T_A > 55^\circ\text{C}$	Derate at 6.67		mW/ $^\circ\text{C}$
$T_A = 25^\circ\text{C}$ to 75°C			mW
$T_A > 75^\circ\text{C}$			mW/ $^\circ\text{C}$
Collector to Emitter Voltage, V_{CEO}	15		V
Collector to Base Voltage, V_{CBO}	20		V
Collector to Substrate Voltage, V_{CIO} (Note 2)	20		V
Emitter to Base Voltage, V_{EBO}	5		V
Collector Current, I_C	50		mA
Operating Temperature Range	-40 $^\circ\text{C}$ to +85 $^\circ\text{C}$		
Storage Temperature Range	-65 $^\circ\text{C}$ to +85 $^\circ\text{C}$		
Soldering Information			
Dual-In-Line Package Soldering (10 Sec.)	260 $^\circ\text{C}$		
Small Outline Package			
Vapor Phase (60 Seconds)	215 $^\circ\text{C}$		
Infrared (15 Seconds)	220 $^\circ\text{C}$		

See AN-450 "Surface Mounting Methods and Their Effect on Product Reliability" for other methods of soldering surface mount devices.

Electrical Characteristics

($T_A = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Conditions	Limits			Units
		Min	Typ	Max	
Collector to Base Breakdown Voltage ($V_{(BR)CBO}$)	$I_C = 10\ \mu\text{A}$, $I_E = 0$	20	60		V
Collector to Emitter Breakdown Voltage ($V_{(BR)CEO}$)	$I_C = 1\ \text{mA}$, $I_B = 0$	15	24		V
Collector to Substrate Breakdown Voltage ($V_{(BR)CIO}$)	$I_C = 10\ \mu\text{A}$, $I_{CI} = 0$	20	60		V
Emitter to Base Breakdown Voltage ($V_{(BR)EBO}$)	$I_E = 10\ \mu\text{A}$, $I_C = 0$	5	7		V
Collector Cutoff Current (I_{CBO})	$V_{CB} = 10\text{V}$, $I_E = 0$		0.002	40	nA
Collector Cutoff Current (I_{CEO})	$V_{CE} = 10\text{V}$, $I_B = 0$			0.5	μA
Static Forward Current Transfer Ratio (Static Beta) (h_{FE})	$V_{CE} = 3\text{V}$ $I_C = 10\ \text{mA}$ $I_C = 1\ \text{mA}$ $I_C = 10\ \mu\text{A}$		100 40 54		
Input Offset Current for Matched Pair Q_1 and Q_2 $ I_{O1} - I_{O2} $	$V_{CE} = 3\text{V}$, $I_C = 1\ \text{mA}$		0.3	2	μA
Base to Emitter Voltage (V_{BE})	$V_{CE} = 3\text{V}$ $I_E = 1\ \text{mA}$ $I_E = 10\ \text{mA}$		0.715 0.800		V
Magnitude of Input Offset Voltage for Differential Pair $ V_{BE1} - V_{BE2} $	$V_{CE} = 3\text{V}$, $I_C = 1\ \text{mA}$		0.45	5	mV
Magnitude of Input Offset Voltage for Isolated Transistors $ V_{BE3} - V_{BE4} $, $ V_{BE4} - V_{BE5} $, $ V_{BE5} - V_{BE3} $	$V_{CE} = 3\text{V}$, $I_C = 1\ \text{mA}$		0.45	5	mV
Temperature Coefficient of Base to Emitter Voltage $\left(\frac{\Delta V_{BE}}{\Delta T}\right)$	$V_{CE} = 3\text{V}$, $I_C = 1\ \text{mA}$		-1.9		mV/ $^\circ\text{C}$
Collector to Emitter Saturation Voltage ($V_{CE(SAT)}$)	$I_B = 1\ \text{mA}$, $I_C = 10\ \text{mA}$		0.23		V

Electrical Characteristics (Continued)

($T_A = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Conditions	Limits			Units
		Min	Typ	Max	
Temperature Coefficient of Input Offset Voltage $\left(\frac{\Delta V_{10}}{\Delta T}\right)$	$V_{CE} = 3\text{V}, I_C = 1\text{mA}$		1.1		$\mu\text{V}/^\circ\text{C}$

Note 1: "Absolute Maximum Ratings" indicate limits beyond which damage to the device may occur. Operating Ratings indicate conditions for which the device is functional, but do not guarantee specific performance limits.

Note 2: The collector of each transistor is isolated from the substrate by an integral diode. The substrate (terminal 13) must be connected to the most negative point in the external circuit to maintain isolation between transistors and to provide for normal transistor action.

Electrical Characteristics

Parameter	Conditions	Min	Typ	Max	Units
Low Frequency Noise Figure (NF)	$f = 1\text{kHz}, V_{CE} = 3\text{V}, I_C = 100\mu\text{A}, R_S = 1\text{k}\Omega$		3.25		dB

LOW FREQUENCY, SMALL SIGNAL EQUIVALENT CIRCUIT CHARACTERISTICS

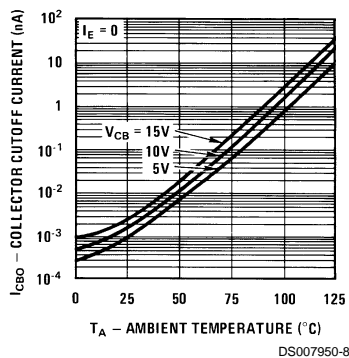
Forward Current Transfer Ratio (h_{fe})	$f = 1\text{kHz}, V_{CE} = 3\text{V}, I_C = 1\text{mA}$		110		
Short Circuit Input Impedance (h_{ie})			3.5		$\text{k}\Omega$
Open Circuit Output Impedance (h_{oe})			15.6		μmho
Open Circuit Reverse Voltage Transfer Ratio (h_{re})			1.8×10^{-4}		

ADMITTANCE CHARACTERISTICS

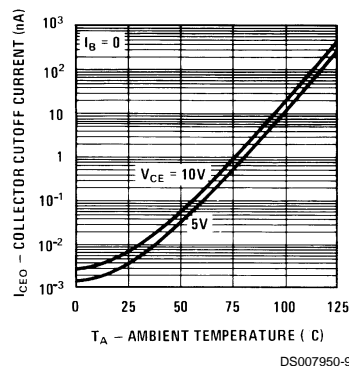
Forward Transfer Admittance (Y_{fe})	$f = 1\text{MHz}, V_{CE} = 3\text{V}, I_C = 1\text{mA}$		$31 - j 1.5$		
Input Admittance (Y_{ie})			$0.3 + j 0.04$		
Output Admittance (Y_{oe})			$0.001 + j 0.03$		
Reverse Transfer Admittance (Y_{re})			See Curve		
Gain Bandwidth Product (f_T)	$V_{CE} = 3\text{V}, I_C = 3\text{mA}$	300	550		
Emitter to Base Capacitance (C_{EB})	$V_{EB} = 3\text{V}, I_E = 0$		0.6		pF
Collector to Base Capacitance (C_{CB})	$V_{CB} = 3\text{V}, I_C = 0$		0.58		pF
Collector to Substrate Capacitance (C_{CI})	$V_{CS} = 3\text{V}, I_C = 0$		2.8		pF

Typical Performance Characteristics

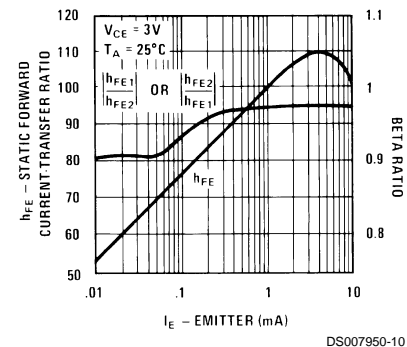
Typical Collector To Base Cutoff Current vs Ambient Temperature for Each Transistor



Typical Collector To Emitter Cutoff Current vs Ambient Temperature for Each Transistor

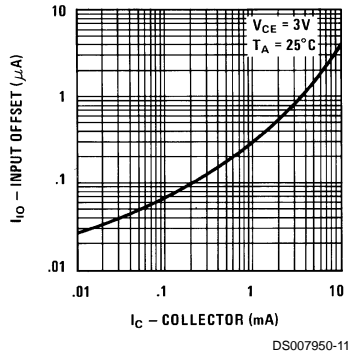


Typical Static Forward Current-Transfer Ratio and Beta Ratio for Transistors Q_1 and Q_2 vs Emitter Current



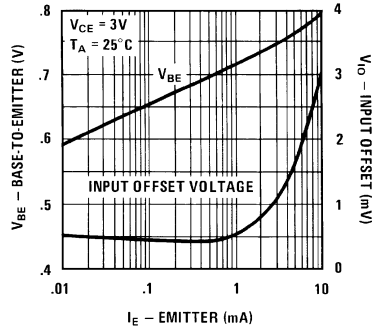
Typical Performance Characteristics (Continued)

Typical Input Offset Current for Matched Transistor Pair Q_1 Q_2 vs Collector Current



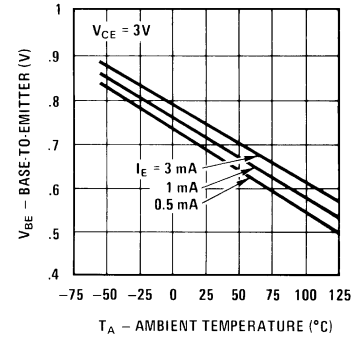
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Typical Static Base To Emitter Voltage Characteristic and Input Offset Voltage for Differential Pair and Paired Isolated Transistors vs Emitter Current



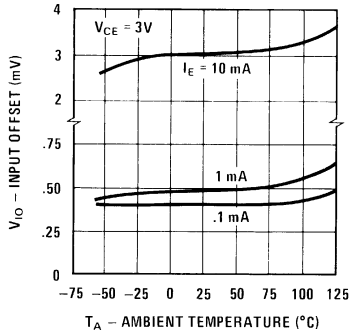
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Typical Base To Emitter Voltage Characteristic for Each Transistor vs Ambient Temperature



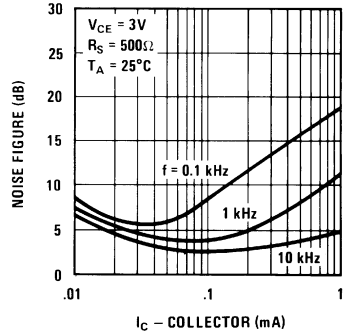
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Typical Input Offset Voltage Characteristics for Differential Pair and Paired Isolated Transistors vs Ambient Temperature



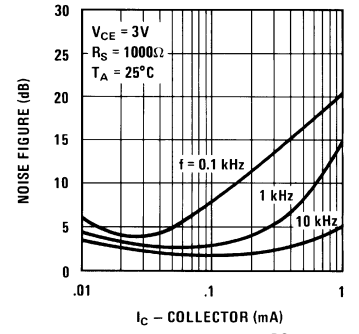
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Typical Noise Figure vs Collector Current



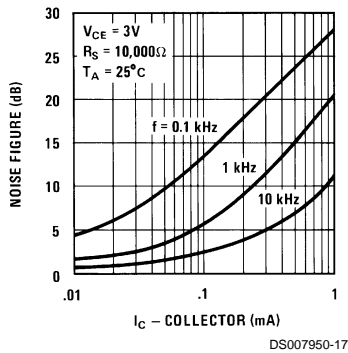
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Typical Noise Figure vs Collector Current



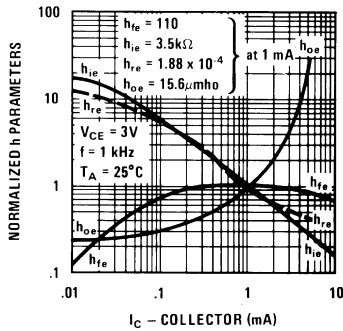
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Typical Noise Figure vs Collector Current



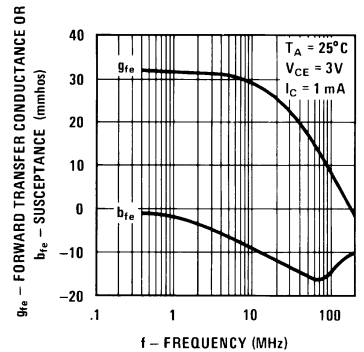
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Typical Normalized Forward Current Transfer Ratio, Short Circuit Input Impedance, Open Circuit Output Impedance, and Open Circuit Reverse Voltage Transfer Ratio vs Collector Current



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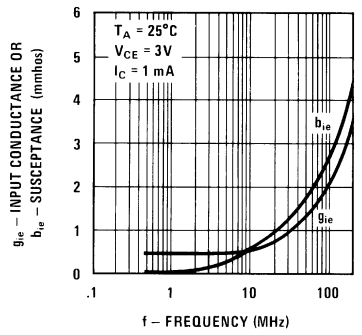
Typical Forward Transfer Admittance vs Frequency



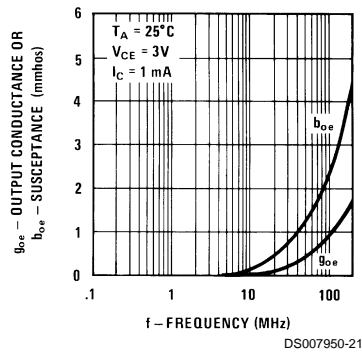
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Typical Performance Characteristics (Continued)

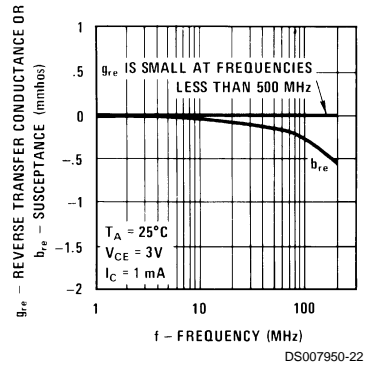
Typical Input Admittance vs Frequency



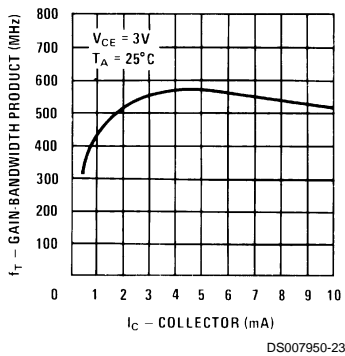
Typical Output Admittance vs Frequency



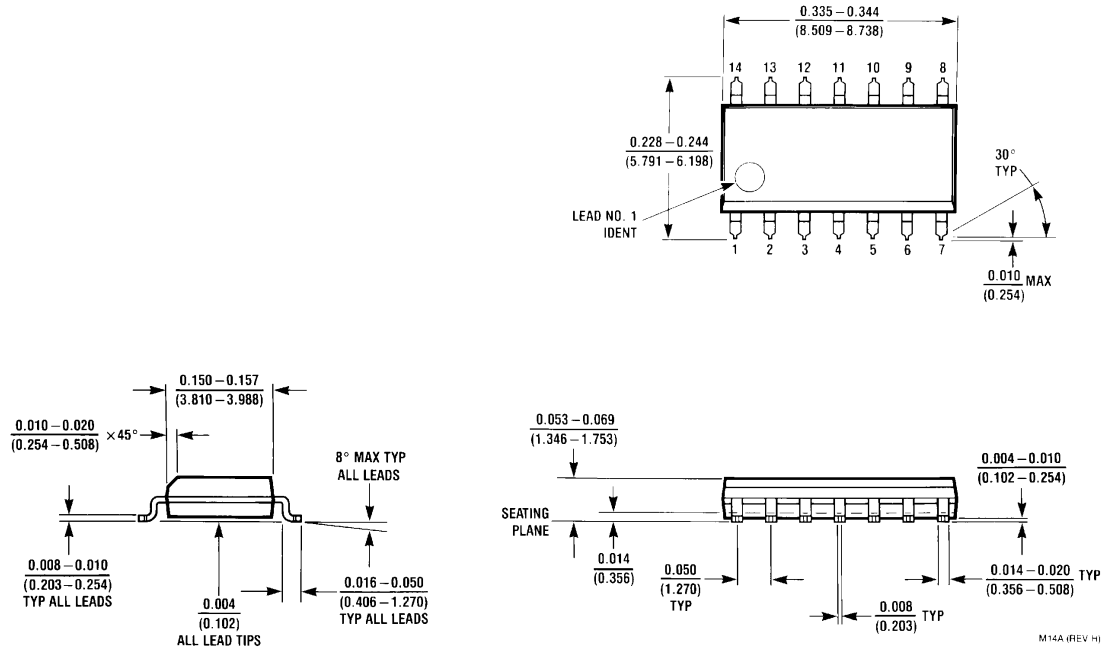
Typical Reverse Transfer Admittance vs Frequency



Typical Gain-Bandwidth Product vs Collector Current



Physical Dimensions inches (millimeters) unless otherwise noted



Molded Small Outline Package (M)
Order Number LM3046M
NS Package Number M14A

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